

Notice of References Cited	Application/Control No. 10/729,732		Applicant(s)/Patent Under Reexamination KAMAL ET AL.	
	Examiner Evan Pert		Art Unit 2826	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,884,681 B1	04-2005	Kamal et al.	438/258
	B	US-6,872,609 B1	03-2005	Kamal et al.	438/194
	C	US-2003/0232507 A1	12-2003	Chen, Cheng Shun	438/763
	D	US-5,418,176	05-1995	Yang et al.	438/262
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Mori et al., "ONO inter-poly dielectric scaling for nonvolatile memory applications", Feb. 1991, IEEE Transactions on Electron Devices, Vol. 38, Issue 2, pages 386-391.
	V	Cheng-Sheng et al., "A scaling methodology for oxide-nitride-oxide interpoly dielectric for EPROM applications", June 1990, IEEE Transactions on Electron Devices, pages 1439-1443.
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.